

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N3567 PN3567
2N3568 PN3568
2N3569 PN3569

JEDEC TO-105 JEDEC TO-92 (EBC)

SILICON NPN TRANSISTORS

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3567, PN3567 Series types are Silicon NPN Small Signal Transistors designed for general purpose amplifier applications.

MAXIMUM RATINGS (T_A=25°C)

	2N3567 PN3567	2N3568 PN3568	2N3569 PN3569	UNIT
Collector-Base Voltage	V _{CB0}	80	80	V
Collector-Emitter Voltage	V _{CEO}	60	40	V
Emitter-Base Voltage	V _{EB0}	5.0	5.0	V
Collector Current	I _C	500	500	mA
Base Current	I _B	100	100	mA
Power Dissipation, PN Types (TO-92 Case)	P _D	625		mW
Power Dissipation, 2N Types (TO-105 Case)	P _D	350		mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-55 TO +150		°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3567 PN3567		2N3568 PN3568		2N3569 PN3569		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =40V		50		50		50	nA
I _{CBO}	V _{CB} =40V, T _A =75°C		5.0		5.0		5.0	μA
I _{EBO}	V _{EB} =4.0V		25		25		25	nA
BV _{CB0}	I _C =100μA	80		80		80		V
BV _{CEO}	I _C =30mA	40		60		40		V
BV _{EB0}	I _E =10μA	5.0		5.0		5.0		V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.25		0.25		0.25	V
V _{BE(ON)}	V _{CE} =1.0V, I _C =150mA		1.1		1.1		1.1	V
h _{FE}	V _{CE} =1.0V, I _C =30mA	40		40		100		
h _{FE}	V _{CE} =1.0V, I _C =150mA	40	120	40	120	100	300	
C _{ob}	V _{CB} =10V, f=140kHz		20		20		20	pF
C _{eb}	V _{EB} =0.5V, f=140kHz		80		80		80	pF
f _T	V _{CE} =10V, I _C =50mA, f=20MHz	60	600	60	600	60	600	MHz